

#### ■ Features

High Voltage Operation: VDS=50VHigh Power: 50.8dBm (typ.) @ Psat

· Proven Reliability

## Description

Sumitomo Electric's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power amplifiers with 50V operation, and gives you higher gain.

This new product is ideally suited for use from  $1.8 \, \mathrm{GHz}$  to  $2.2 \, \mathrm{GHz}$  W-CDMA and LTE design requirements as it offers high gain, long term reliability and ease of use.



ABSOLUTE MAXIMUM RATINGS ( Case Temperature T<sub>c</sub>=25deg.C )

ADSOLUTE MAXIMUM KATIN	d5   case remperature r <sub>c</sub> =25deg.c			
Item	Symbol	Condition	Rating	Unit
Operating Voltage	$V_{DS}$		55	V
Drain-Source Voltage	$V_{DS}$	V <sub>GS</sub> =-8V	160	V
Gate-Source Voltage	$V_{GS}$		-15	V
Total Power Dissipation	P <sub>t</sub>		97.8	W
Storage Temperature	T <sub>stg</sub>		-65 to +175	deg.C
Channel Temperature	T <sub>ch</sub>		250	deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	$V_{DS}$		<u>&lt;</u> 55	V
Forward Gate Current	$I_{GF}$	R <sub>G</sub> =5 ohm	<u>&lt;</u> 95	mA
Reverse Gate Current	$I_{GR}$	R <sub>G</sub> =5 ohm	<u>&gt;</u> -3.5	mA
Channel Temperature	T <sub>ch</sub>		<u>&lt;</u> 200	deg.C
Average Output Power	P <sub>ave</sub> .		<u>&lt;</u> 47.5	dBm

ELECTRICAL CHARACTERISTICS ( Case Temperature  $T_c = 25 \text{deg.C}$  )

Item	Symbol	Condition		Limit		
	Symbol		Min.	Typ.	Max.	Unit
Pinch-Off Voltage	$V_p$	$V_{DS}$ =50V $I_{DS}$ =24mA	-4.0	-	-2.0	V
Saturated Power	Psat *1	V <sub>DS</sub> =50V	50.0	50.8	-	dBm
Drain Efficiency	ηD *2	$I_{DS(DC)}$ =400mA	27.0	31.0	-	%
Power Gain	Gp *2	f=2.17GHz	15.0	16.0	-	dB
Drain Efficiency at Psat	DE *1	I <sub>DS(DC)</sub> =0mA f=2.17GHz	59.0	65.0	-	%
Thermal Resistance	R <sub>th</sub>	Channel to Case at 52.5W Ppc	-	1.7	2.0	deg.C/W

<sup>\*1:10%-</sup>duty RF pulse ( DC supply constant )

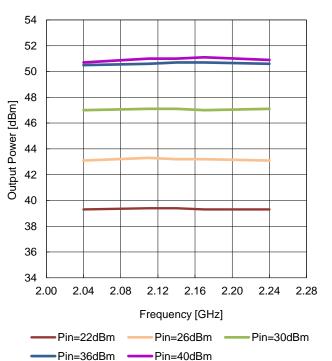
<sup>\*2 :</sup> Pout=43dBm, CW modulation Signal ( W-CDMA )

RoHS Compliance	YES



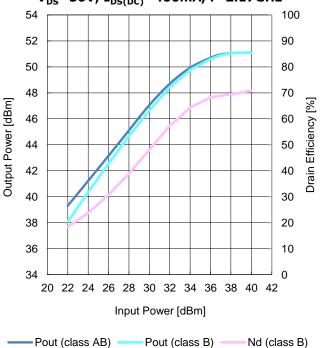
### RF characteristics @f=2.17GHz fine tuned

## **Output Power vs. Frequency** $V_{DS} = 50V, I_{DS(DC)} = 400mA$



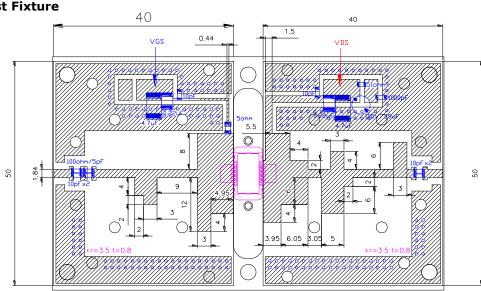
# **Input Power** $V_{DS} = 50V$ , $I_{DS(DC)} = 400mA$ , f = 2.17GHz

**Output Power and Drain Efficiency vs.** 



## Pulse Signal (10%-duty, DC: constant)

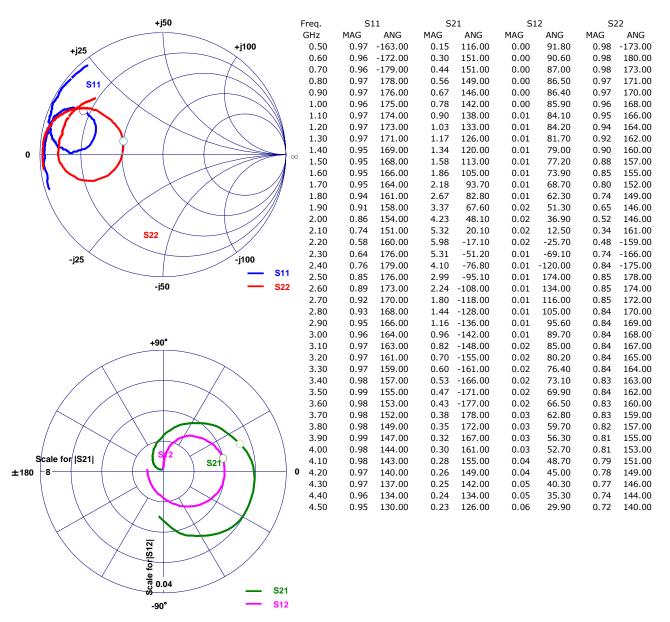
# **Test Fixture**





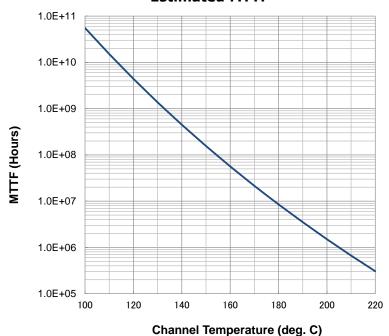
### - Reference DATA -

S-Parameters @VDS=50V, IDS(DC)=400mA, f=0.5 to 4.5GHz ZI = Zs = 500hm Marker : 2.14GHz





MTTF Calculation
- Estimated MTTF -



Ea=1.6eV Confidence Level=90%

Channel Temp (deg.C)	MTTF (Hours)
160	5.98 x 10 <sup>7</sup>
180	9.02 x 10 <sup>6</sup>
200	1.60 x 10 <sup>6</sup>

AF=exp[(-Ea/k)(1/T<sub>stress</sub>-1/T<sub>use</sub>)

 $\mathsf{MTTF}_{\mathsf{use}} = \mathsf{MTTF}_{\mathsf{stress}} * \mathsf{AF}$ 

Where:

AF: acceleration factor

Ea: activation energy (1.6 eV)

k: Boltzman's constant (8.62 x 10<sup>-5</sup> eV/K)

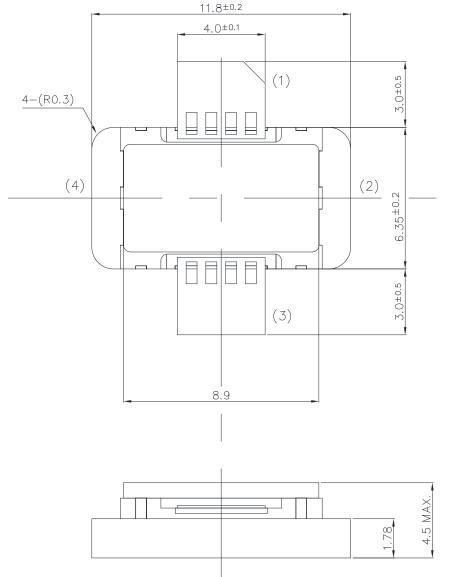
 $T_{stress}$ : stress temperature (K)  $T_{use}$ : use temperature (K)

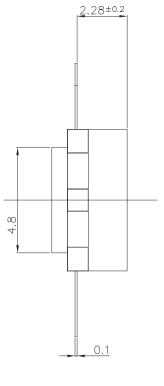
### **ESD** characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	1A
Machine Model (per JEIA/ESD22-A115)	A
Device Charged Model (per JESD22-C101)	IV



### M1H Package Outline Metal-Ceramic Hermetic Package





- 1. Gate
- 2. Source
- 3. Drain
- 4. Source

Unit: mm

Talerance:  $\pm 0.15$ 



## For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
   This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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Information in this document is subject to change without notice.

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